

TOSHIBA Field Effect Transistor Silicon P, N Channel MOS Type (U-MOS IV / U-MOS III)

# TPCF8402

Portable Equipment Applications  
 Motor Drive Applications  
 DC-DC Converter Applications

- Low drain-source ON resistance  
 : P Channel  $R_{DS(ON)} = 60 \text{ m}\Omega$  (typ.)  
 N Channel  $R_{DS(ON)} = 38 \text{ m}\Omega$  (typ.)
- High forward transfer admittance  
 : P Channel  $|Y_{fs}| = 5.9 \text{ S}$  (typ.)  
 N Channel  $|Y_{fs}| = 6.8 \text{ S}$  (typ.)
- Low leakage current  
 : P Channel  $I_{DSS} = -10 \text{ }\mu\text{A}$  ( $V_{DS} = -30 \text{ V}$ )  
 N Channel  $I_{DSS} = 10 \text{ }\mu\text{A}$  ( $V_{DS} = 30 \text{ V}$ )
- Enhancement-mode  
 : P Channel  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )  
 N Channel  $V_{th} = 1.3 \text{ to } 2.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

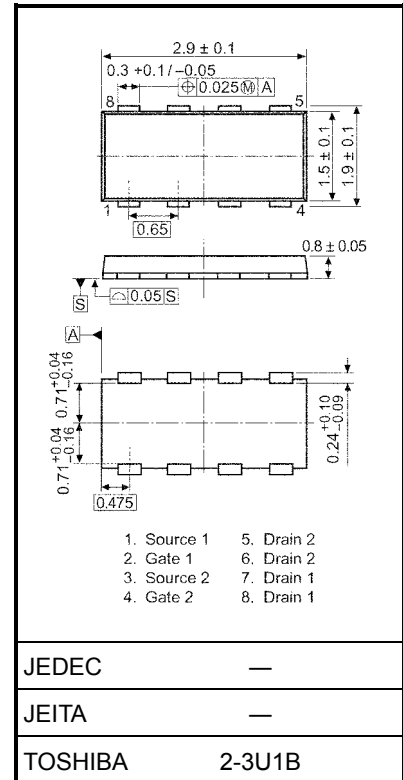
## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating		Unit
Drain-source voltage		$V_{DSS}$	-30	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-30	30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-3.2	4.0	A
	Pulse (Note 1)	$I_{DP}$	-12.8	16.0	
Drain power dissipation ( $t = 5 \text{ s}$ ) (Note 2a)	Single-device operation (Note 3a)	$P_D(1)$	1.35	1.35	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	1.12	1.12	
Drain power dissipation ( $t = 5 \text{ s}$ ) (Note 2b)	Single-device operation (Note 3a)	$P_D(1)$	0.53	0.53	
	Single-device value at dual operation (Note 3b)	$P_D(2)$	0.33	0.33	
Single pulse avalanche energy (Note 4)		$E_{AS}$	0.67	2.6	mJ
Avalanche current		$I_{AR}$	-1.6	2.0	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		$E_{AR}$	0.11		mJ
Channel temperature		$T_{ch}$	150		$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55~150		$^\circ\text{C}$

Note: For (Note 1), (Note 2), (Note 3), (Note 4), (Note 5) and (Note 6), please refer to the next page.

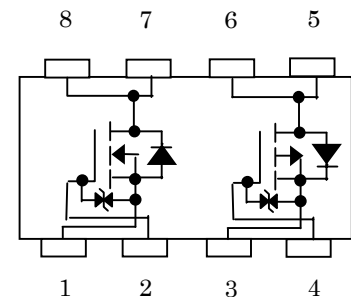
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

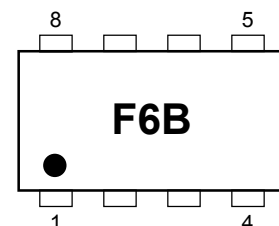


Weight: 0.011 g (typ.)

## Circuit Configuration



## Marking (Note 6)

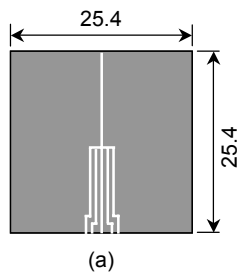


## Thermal Characteristics

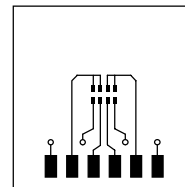
Characteristics		Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	R <sub>th (ch-a) (1)</sub>	92.6	°C/W
	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	111.6	
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	R <sub>th (ch-a) (1)</sub>	235.8	°C/W
	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	378.8	

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)



FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)

Note 3: a) The power dissipation and thermal resistance values are shown for a single device (During single-device operation, power is only applied to one device.).

b) The power dissipation and thermal resistance values are shown for a single device (During dual operation, power is evenly applied to both devices.).

Note 4: P Channel: V<sub>DD</sub> = -24 V, T<sub>ch</sub> = 25°C (initial), L = 0.2 mH, R<sub>G</sub> = 25 Ω, I<sub>AR</sub> = -1.6 A  
N Channel: V<sub>DD</sub> = 24 V, T<sub>ch</sub> = 25°C (initial), L = 0.5 mH, R<sub>G</sub> = 25 Ω, I<sub>AR</sub> = 2.0 A

Note 5: Repetitive rating; Pulse width limited by Max. Channel temperature.

Note 6: Black round marking “ ” locates on the left lower side of parts number marking “F6B indicates terminal No. 1.

## P-ch

### Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4.5 \text{ V}, I_D = -1.6 \text{ A}$	—	80	105	m $\Omega$
			$V_{GS} = -10 \text{ V}, I_D = -1.6 \text{ A}$	—	60	72	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -1.6 \text{ A}$	2.9	5.9	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	600	—	pF
Reverse transfer capacitance		$C_{rss}$		—	60	—	
Output capacitance		$C_{oss}$		—	70	—	
Switching time	Rise time	$t_r$		—	5.3	—	ns
	Turn-on time	$t_{on}$		—	12	—	
	Fall time	$t_f$		—	8.4	—	
	Turn-off time	$t_{off}$		—	34	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} = -24 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -3.2 \text{ A}$	—	14	—	nC
Gate-source charge 1		$Q_{gs1}$		—	1.4	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	2.7	—	

### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-12.8	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -3.2 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

## N-ch

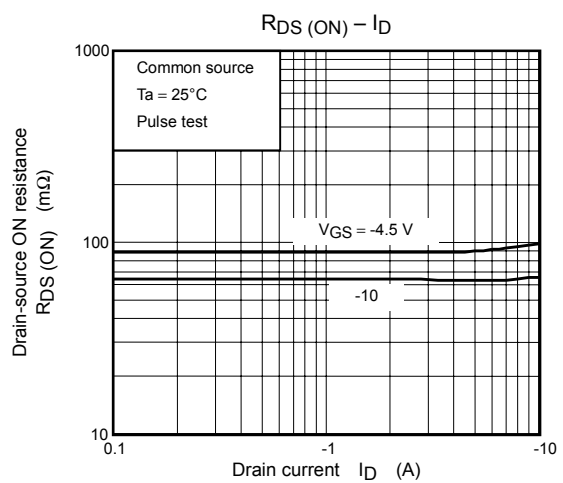
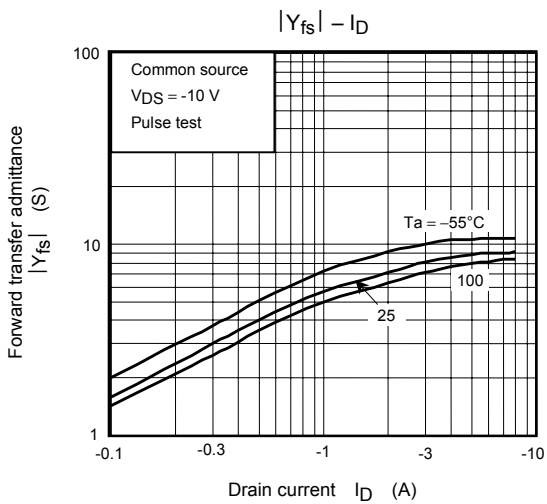
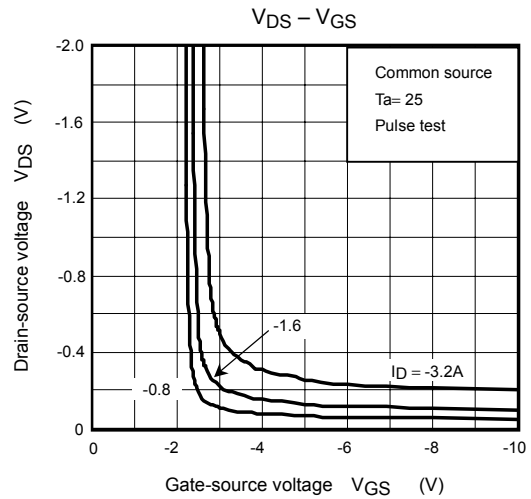
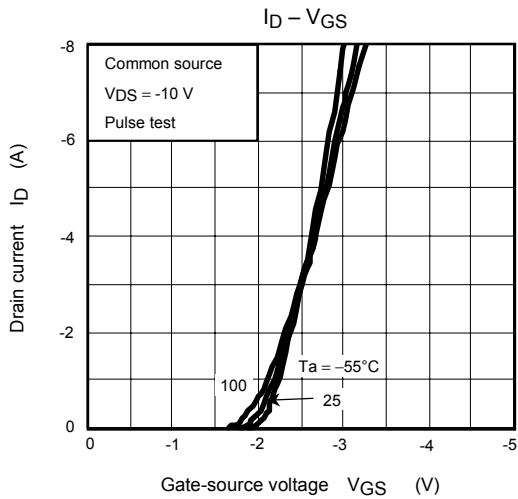
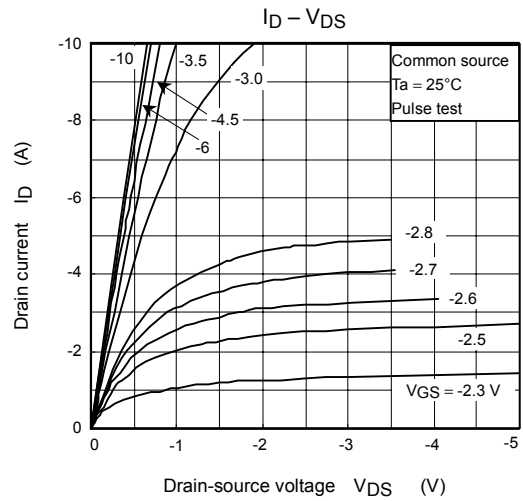
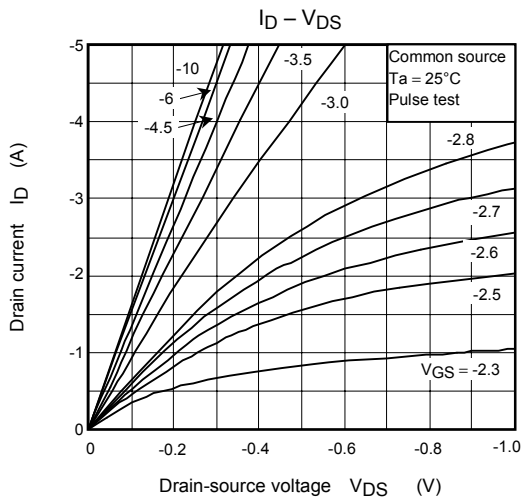
### Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.3	—	2.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4.5 \text{ V}, I_D = 2.0 \text{ A}$	—	58	77	m $\Omega$
			$V_{GS} = 10 \text{ V}, I_D = 2.0 \text{ A}$	—	38	50	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 2.0 \text{ A}$	3.4	6.8	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	470	—	pF
Reverse transfer capacitance		$C_{rss}$		—	60	—	
Output capacitance		$C_{oss}$		—	80	—	
Switching time	Rise time	$t_r$		—	5.2	—	ns
	Turn-on time	$t_{on}$		—	8.3	—	
	Fall time	$t_f$		—	4.0	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10 \mu\text{s}$	—	22	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	—	10	—	nC
Gate-source charge 1		$Q_{gs1}$		—	1.7	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	2.4	—	

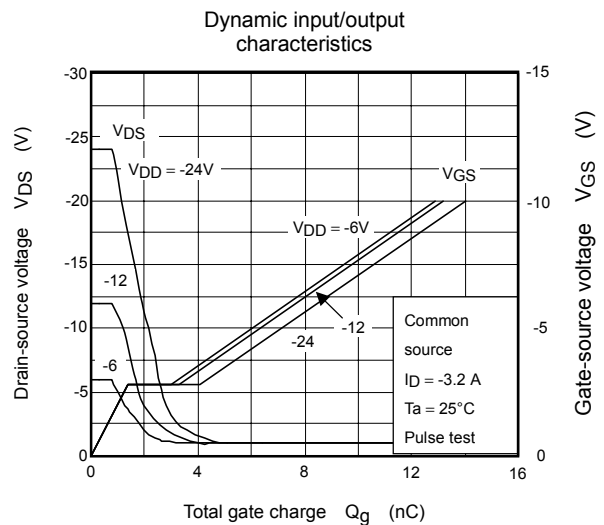
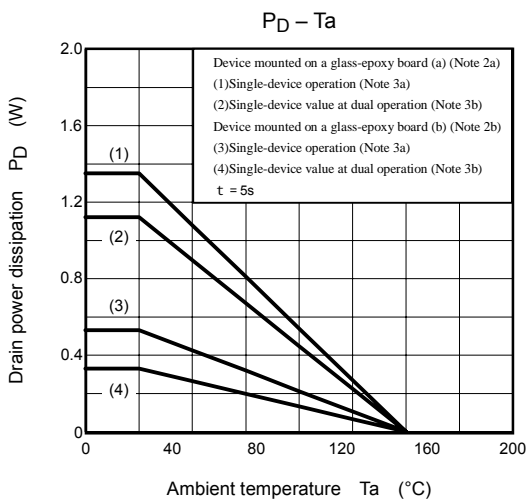
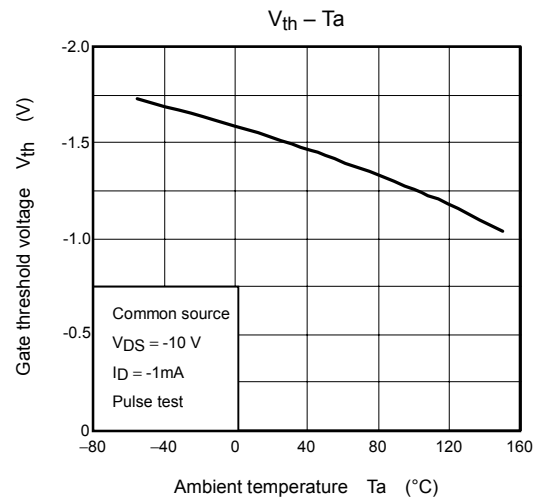
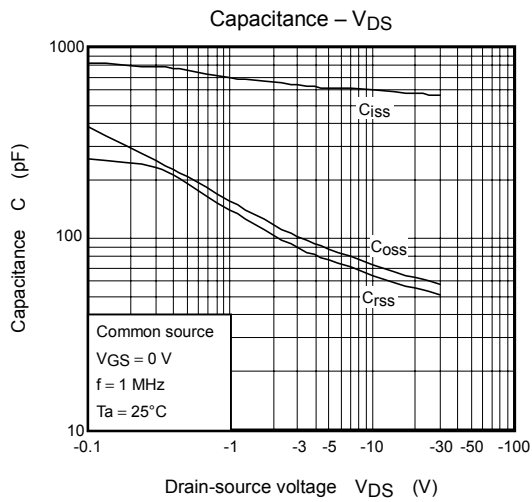
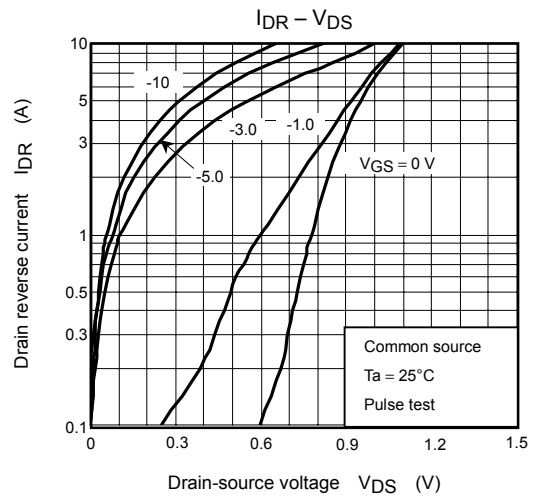
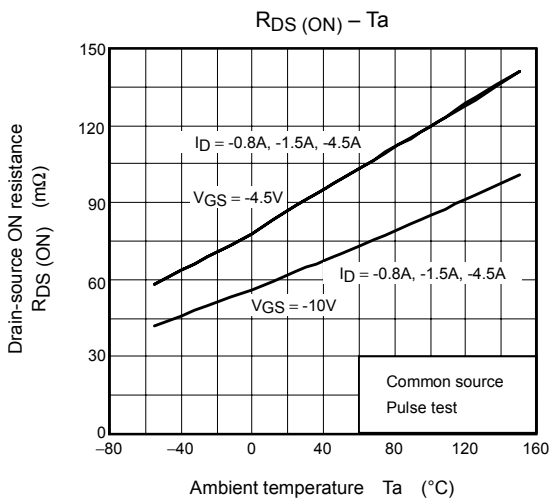
### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	16.0	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 4.0 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V

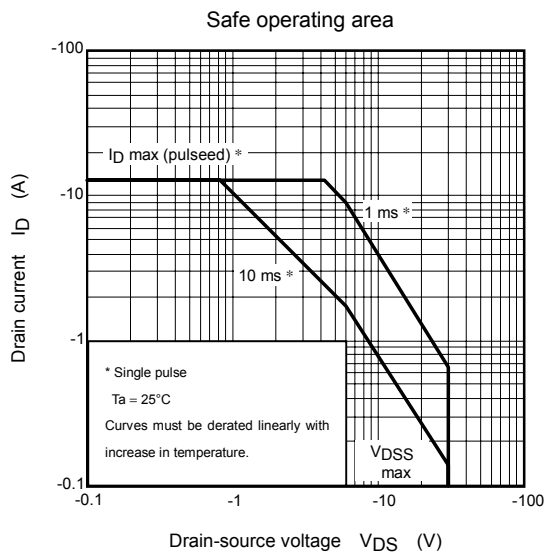
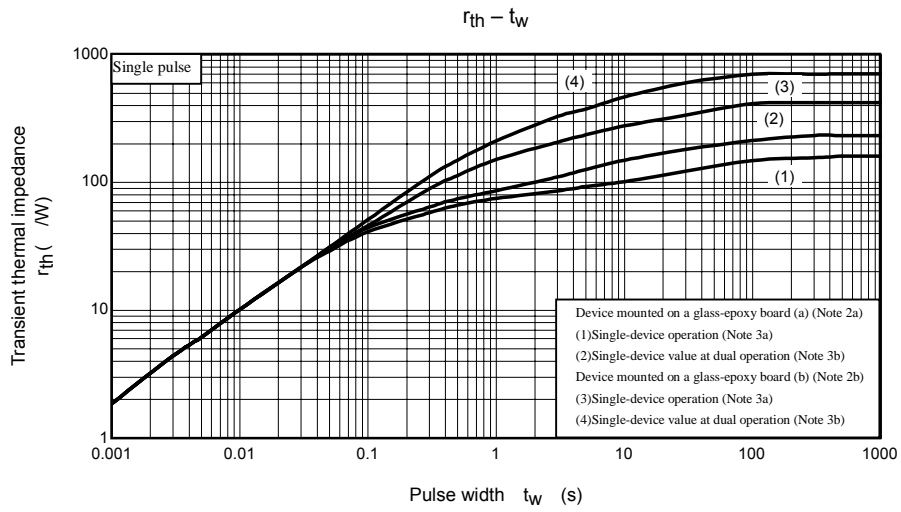
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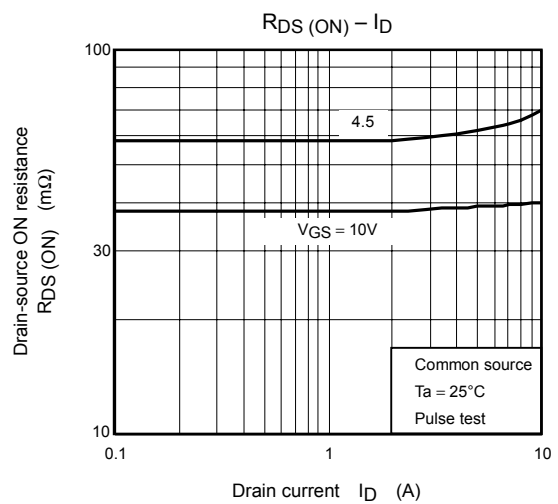
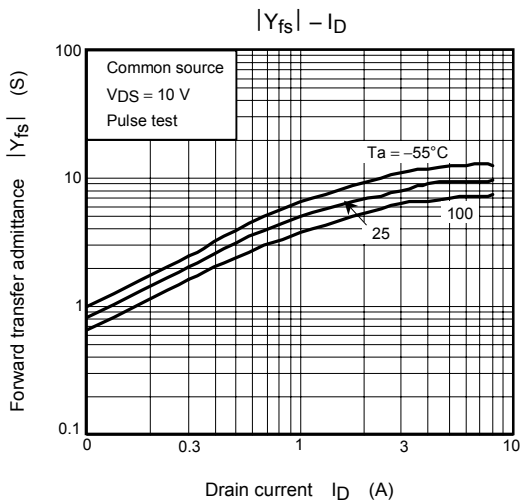
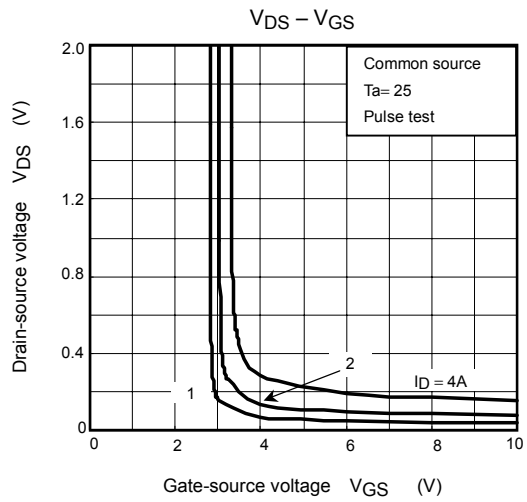
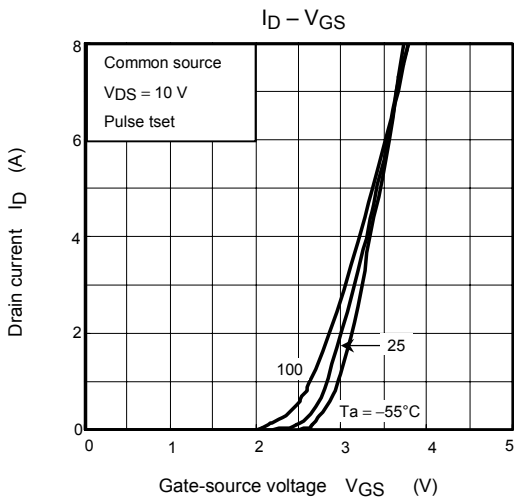
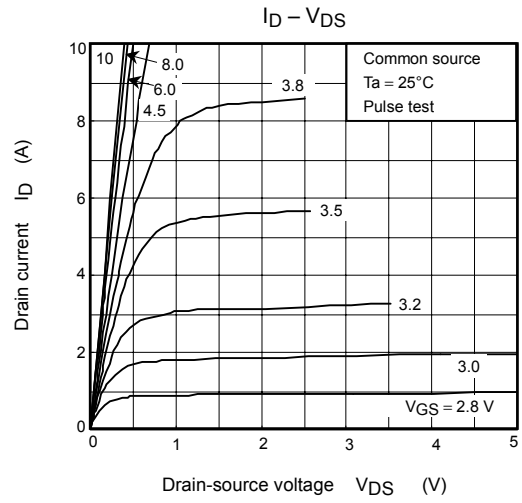
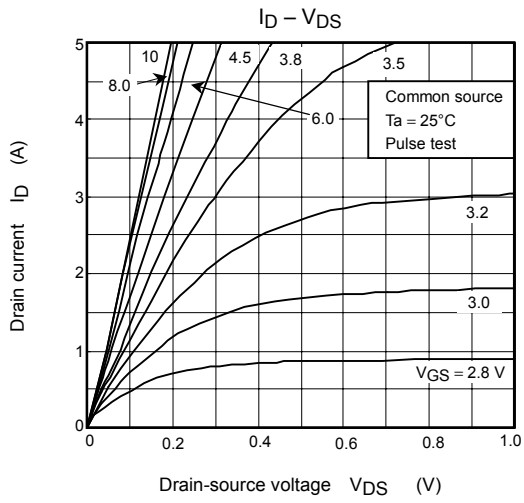
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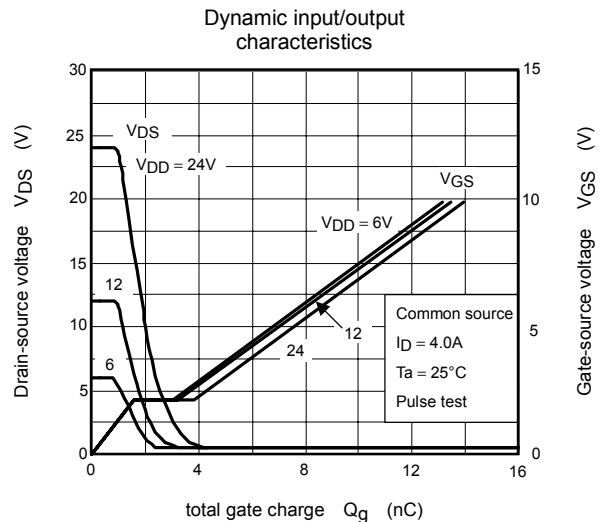
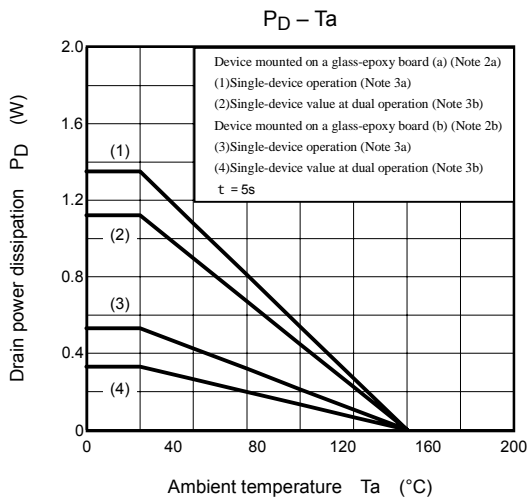
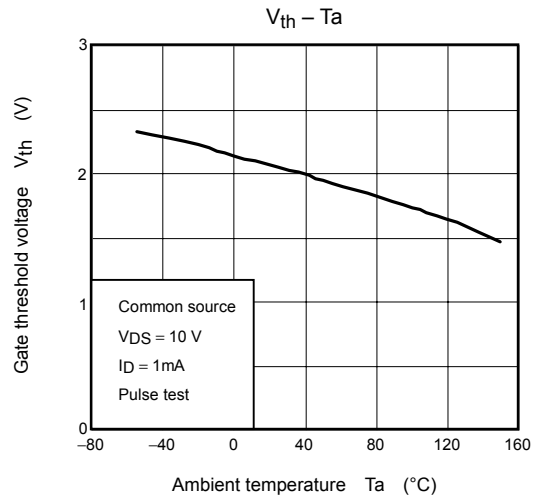
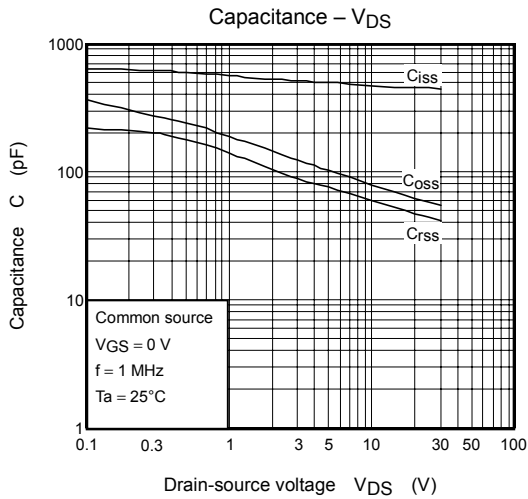
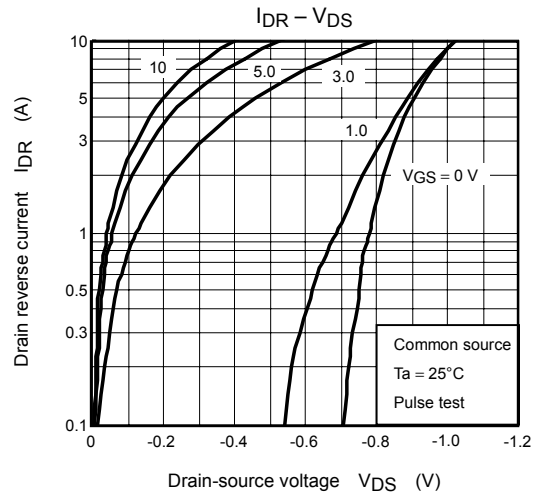
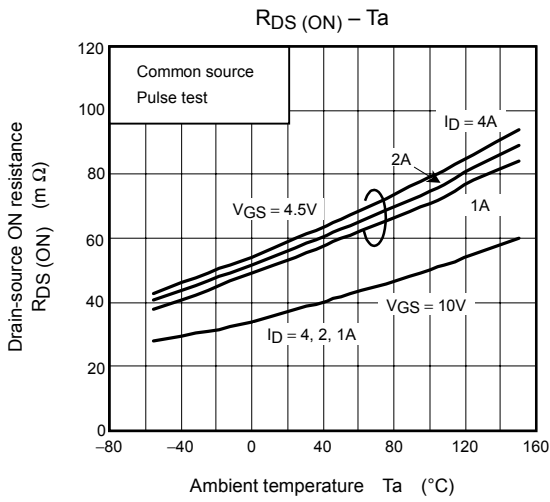


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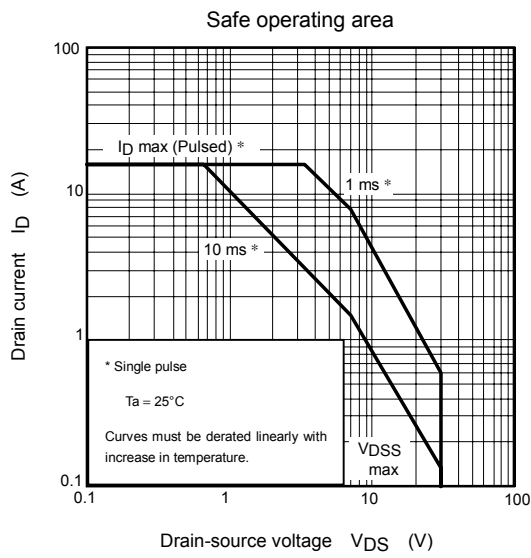
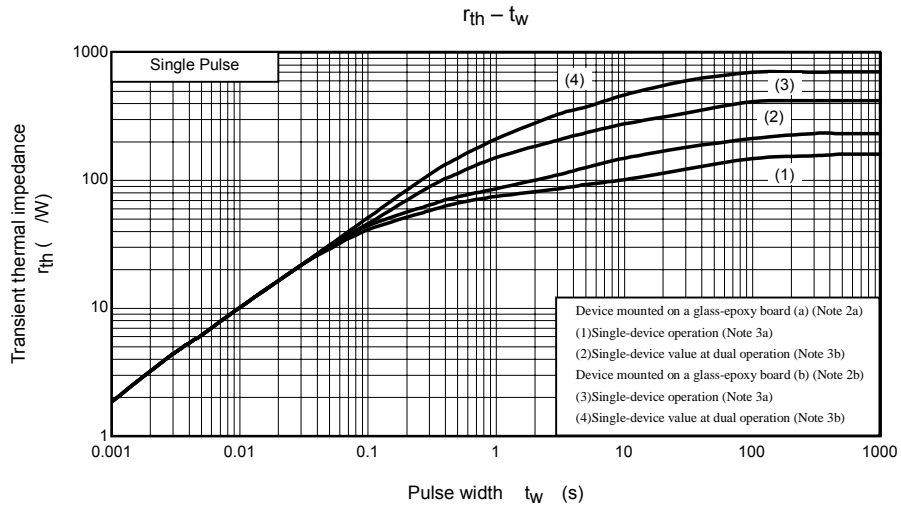




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